



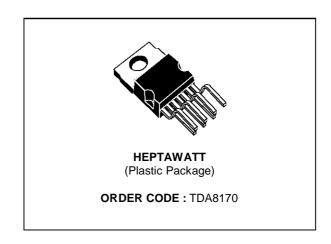
TV VERTICAL DEFLECTION OUTPUT CIRCUIT

The functions incorporated are:

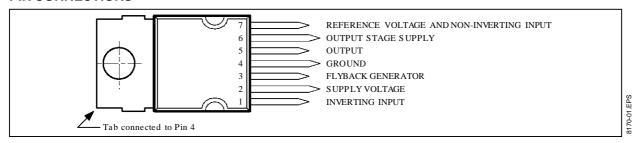
- POWER AMPLIFIER
- FLYBACK GENERATOR
- REFERENCE VOLTAGE
- THERMAL PROTECTION

DESCRIPTION

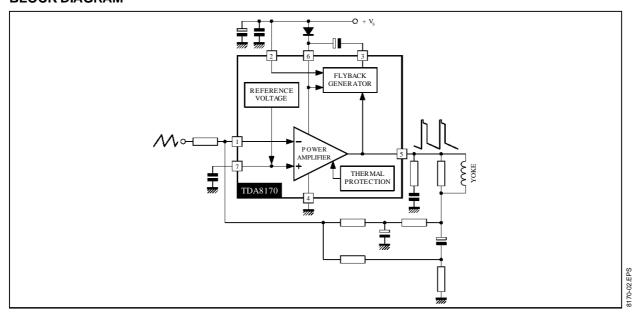
The TDA8170 is a monolithic integrated circuit in HEPTAWATTTM package. It is a high efficiency power booster for direct driving of vertical windings of TV yokes. It is intended for use in Colour and B & W television receivers as well as in monitors and displays.



PIN CONNECTIONS

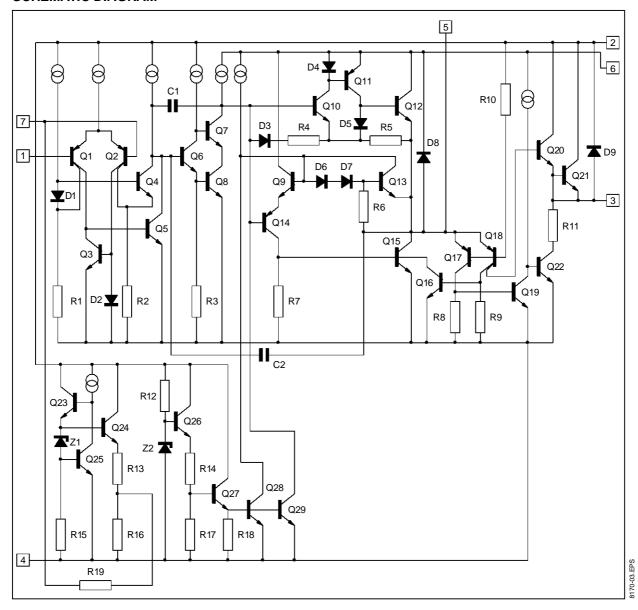


BLOCK DIAGRAM



May 1996 1/7

SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage (pin 2)	35	V
V ₅ , V ₆	Flyback Peak Voltage	60	V
V ₃	Voltage at Pin 3	+ V _s	
V ₁ , V ₇	Amplifier Input Voltage	+ V _s - 0.5	V
lo	Output Peak Current (non repetitive, t = 2 msec)	2.5	Α
lo	Output Peak Current at f = 50 or 60 Hz, $t \le 10 \mu sec$	3	Α
lo	Output Peak Current at f = 50 or 60 Hz, t > 10 μsec	2	Α
l ₃	Pin 3 DC Current at V ₅ < V ₂	100	mA
l ₃	Pin 3 Peak to Peak Flyback Current at f= 50 or 60 Hz, t _{fly} ≤1.5msec	3	Α
P _{tot}	Total Power Dissipation at T _{case} = 90 °C	20	W
T _{stg} , T _j	Storage and Junction Temperature	- 40 to 150	°C

THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th j-case}	Thermal Resistance Junction-case Max.	3	°C/W

ELECTRICAL CHARACTERISTICS

(refer to the test circuits, $V_S = 35V$, $T_{amb} = 25$ °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	Fig.
I_2	Pin 2 Quiescent Current	$I_3 = 0, I_5 = 0$		8	16	mA	1a
l ₆	Pin 6 Quiescent Current	$I_3 = 0, I_5 = 0$		16	36	mA	1a
I ₁	Amplifier Input Bias Current	V ₁ = 1 V		- 0.1	- 1	μΑ	1a
V ₇	Reference Voltage			2.2		V	1a
$\frac{\Delta V_7}{\Delta V_S}$	Reference Voltage Drift versus Supply Voltage	V _s = 15 to 30 V		1	2	mV/V	1a
V _{3L}	Pin 3 Saturation Voltage to GND	I ₃ = 20 mA		1		V	1c
V ₅	Quiescent Output Voltage	$V_s = 35 \text{ V}$, $R_a = 39 \text{ k}\Omega$		18		V	1d
		$V_s = 15 \text{ V}$, $R_a = 13 \text{ k}\Omega$		7.5		V	1d
V_{5L}	Output Saturation Voltage to GND	I ₅ = 1.2 A		1	1.4	V	1c
		I ₅ = 0.7 A		0.7	1	V	1c
V _{5H}	Output Saturation Voltage to Supply	- I ₅ = 1.2 A		1.6	2.2	V	1b
		- I ₅ = 0.7 A		1.3	1.8	V	1b
Tj	Junction Temperature for Thermal Shut Down			140		°C	

Figure 1a : Measurement of I_1 , I_2 , I_6 , V_7 , $\Delta V_7/\Delta V_S$

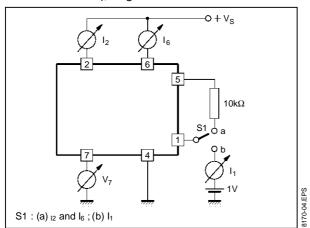


Figure 1b: Measurement of V_{5H}

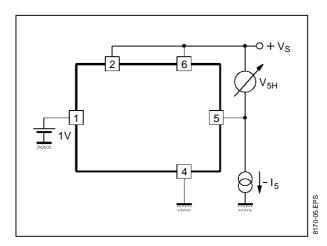


Figure 1c: Measurement of V_{3L} , V_{5L}

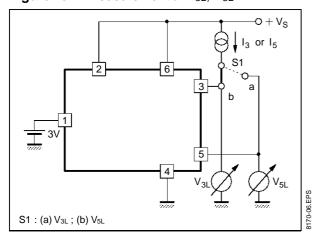


Figure 1d: Measurement of V_5

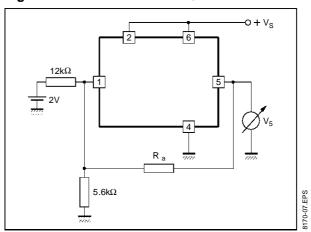


Figure 2: AC Test Circuit

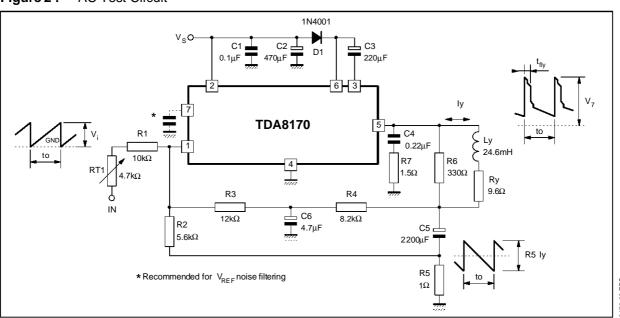


Figure 3: PC Board and Component layout of the Circuit of fig. 2(1:1 scale)

COMPONENTS LIST FOR TYPICAL APPLICATIONS

Component	110 ° TVC 5.9 Ω/10 mH 1.95 App	110 ° TVC 9.6 Ω/24.6 mH 1.2 App	90 ° TVC 15 Ω/30 mH 0.82 App	Unit
RT1	10	4.7	10	kΩ
R1	12	10	12	kΩ
R2	10	5.6	5.6	kΩ
R3	27	12	18	kΩ
R4	12	8.2	5.6	kΩ
R5	0.82	1	1	Ω
R6	270	330	330	Ω
R7	1.5	1.5	1.5	Ω
D1	1N 4001	1N 4001	1N 4001	_
C1	0.1	0.1	0.1	μF
C2 el.	1000/25 V	470/25 V	470/25 V	μF
C3 el.	220/25 V	220/25 V	220/25 V	μF
C4	0.22	0.22	0.22	μF
C5 el.	200/25 V	2200/25 V	1000/16 V	μF
C6 el.	4.7/16 V	4.7/16 V	10/16 V	μF

TYPICAL PERFORMANCES

Parameter	110 ° TVC 5.9 Ω/10 mH	110 ° TVC 9.6 Ω/27 mH	90 ° TVC 15 Ω/30 mH	Unit
V _s - Supply Voltage	24	22.5	25	V
I _s - Current	280	175	125	mA
t _{fly} - Flyback Time	0.6	1	0.7	ms
P _{tot} - Power Dissip.	4.2	2.5	2.05	W
R _{th o-a} - Heatsink	7	13	16	°C/W
T _{amb}	60	60	60	°C
T _{j max}	110	110	110	°C
To	20	20	20	ms
VI	2.5	2.5	2.5	V _{pp}
V ₇	2.5	2.5	2.5	V _p

MOUNTING INSTRUCTIONS

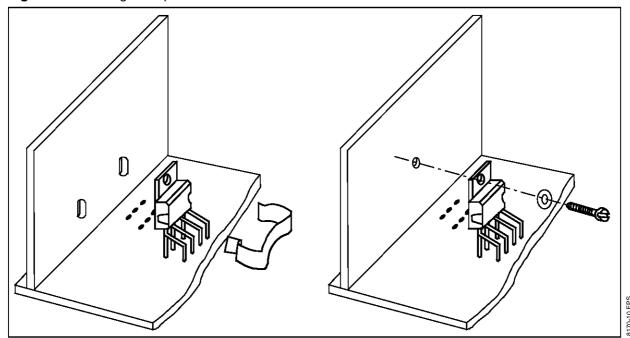
The power dissipated in the circuit must be re-

moved by adding an external heatsink.

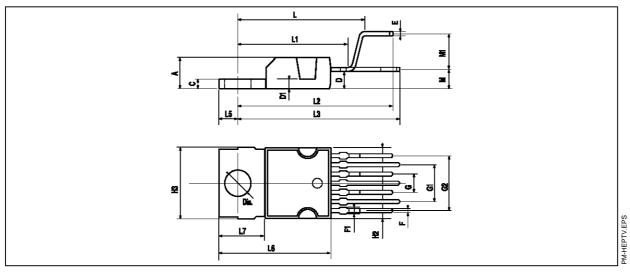
Thanks to the HEPTAWATTTM package attaching the heatsink is very simple, a screw a compression

spring (clip) being sufficient. Between the heatsink and the package it is better to inserta layer of silicon grease, to optimize the thermal contact; no electrical isolation is needed between the two surfaces.

Figure 4: Mounting Examples



PACKAGE MECHANICAL DATA: 7 PINS - PLASTIC HEPTAWATT



Dimensions	Millimeters			Inches		
Dimensions	Min.	Тур.	Max.	Min.	Тур.	Max.
Α			4.8			0.189
С			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		08	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
М		2.8			0.110	
M1		5.08			0.200	
Dia.	3.65		3.85	0.144		0.152

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